

## ABSTRACT

In a multiple input ESD protection structure, the inputs are isolated from the substrate  
5 by highly doped regions of opposite polarity to the input regions. Dual polarity is  
achieved by providing a symmetrical structure with n+ and p+ regions forming each  
dual polarity input. The inputs are formed in a p-well which, in turn, is formed in a n-  
well. Each dual polarity input is isolated by a PBL under the p-well, and a NISO  
underneath the n-well. An isolation ring separates and surrounds the inputs. The  
10 isolation ring comprises a p+ ring or a p+ region, n+ region, and p+ region formed  
into adjacent rings.